

650V 12A Advanced N-Ch Power MOSFET

FEATURES

- High Voltage : $BV_{DSS}=650V(\text{Min.})$
- Low reverse transfer capacitance : $C_{rss}=14.5pF(\text{Typ.})$
- Low gate charge : $Q_g=38nC(\text{Typ.})$
- Low drain-source On resistance : $R_{DS(on)}=0.68\Omega(\text{Typ.})$
- 100% avalanche tested

Marking Information

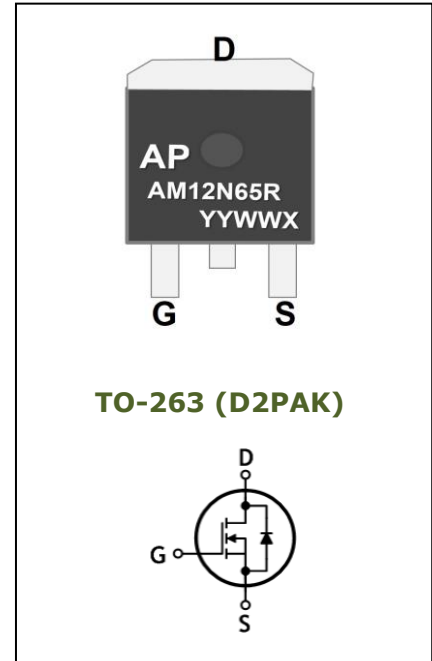
Row 1 : AP

Row 2 : Product Information

Row 3 : Date Code

- YY : Year Code

- WW : Week Code



Ordering Information

Part No	Package	Packing	Finish	Halogen	Packing Unit
AM12N65RD	TO-263(D2PAK)	REEL	Sn	Free	800ea/reel

Maximum Ratings (Tc=25 °C, unless otherwise noted)

Characteristic	Symbol	Rating	Unit
Drain-source voltage	V_{DSS}	650	V
Gate-source voltage	V_{GSS}	± 30	V
Drain current (DC)*	I_D	$T_C = 25^\circ C$	12
		$T_C = 100^\circ C$	9.0
Drain current (Pulsed)*	I_{DM}	48	A
Power Dissipation	P_D	100	W
Avalanche current (Single) (Note 2)	I_{AS}	12	A
Single pulsed avalanche energy (Note 2)	E_{AS}	140	mJ
Avalanche current (Repetitive) (Note 1)	I_{AR}	12	A
Repetitive avalanche energy (Note 1)	E_{AR}	7.6	mJ
Junction temperature	T_J	150	$^\circ C$
Storage temperature range	T_{stg}	-55~150	

*Limited only maximum junction temperature

Thermal Characteristic

Characteristic	Symbol	Rating	Unit
Thermal resistance, junction to case	$R_{th(j-c)}$	Max. 0.8	°C/W
Thermal resistance, junction to ambient	$R_{th(j-a)}$	Max. 62.5	

Electrical Characteristics ($T_C=25\text{ }^{\circ}\text{C}$, unless otherwise noted)

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Drain-source breakdown voltage	BV_{DSS}	$I_D = 250\mu\text{A}$, $V_{GS} = 0$	650	-	-	V
Gate threshold voltage	$V_{GS(th)}$	$I_D = 250\mu\text{A}$, $V_{DS} = V_{GS}$	3	-	5	V
Drain-source cut-off current	I_{DSS}	$V_{DS} = 650\text{V}$, $V_{GS} = 0\text{V}$	-	-	1	μA
Gate leakage current	I_{GSS}	$V_{DS} = 0\text{V}$, $V_{GS} = \pm 30\text{V}$	-	-	± 100	nA
Drain-source on-resistance (Note 4)	$R_{DS(ON)}$	$V_{GS} = 10\text{V}$, $I_D = 6.0\text{A}$	-	0.68	0.80	Ω
Forward transfer conductance (Note 4)	g_{fs}	$V_{DS} = 10\text{V}$, $I_D = 6.0\text{A}$	-	13.5	-	S
Input capacitance	C_{iss}	$V_{DS} = 25\text{V}$, $V_{GS} = 0\text{V}$, $f = 1.0\text{MHz}$	-	2470	3100	pF
Output capacitance	C_{oss}		-	160	-	
Reverse transfer capacitance	C_{rss}		-	14.5	-	
Turn-on delay time (Note 3,4)	$T_{d(on)}$	$V_{DS} = 300\text{V}$, $I_D = 12\text{A}$, $R_G = 25\Omega$	-	38	-	ns
Rise time (Note 3,4)	T_r		-	95	-	
Turn-off delay time (Note 3,4)	$t_{d(off)}$		-	155	-	
Fall time (Note 3,4)	t_f		-	105	-	
Total gate charge (Note 3,4)	Q_g	$V_{DS} = 520\text{V}$, $V_{GS} = 10\text{V}$, $I_D = 12\text{A}$	-	38	45	nC
Gate-source charge (Note 3,4)	Q_{gs}		-	15	-	
Gate-drain charge (Note 3,4)	Q_g		-	9	-	

Source-Drain Diode Ratings and Characteristics ($T_C=25\text{ }^{\circ}\text{C}$, unless otherwise noted)

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Source current (DC)	I_S	Integral reverse diode in the MOSFET	-	-	12	A
Source current (Pulsed) (Note 1)	I_{SM}		-	-	48	A
Forward voltage (Note 4)	V_{SD}	$V_{GS} = 0\text{V}$, $I_S = 12\text{A}$	-	-	1.4	V
Reverse recovery time	t_{rr}	$I_S = 12\text{A}$, $V_{GS} = 0\text{V}$, $dI_F/dt = 100\text{A}/\mu\text{s}$	-	500	-	ns
Reverse recovery charge	Q_{rr}		-	4.3	-	μC

Note :

1. Repetitive rating : Pulse width limited by maximum junction temperature.
2. $L=1.8\text{mH}$, $I_{AS}=12\text{A}$, $V_{DD}=50\text{V}$, $R_G=25\Omega$, Starting $T_J=25^{\circ}\text{C}$
3. Pulse Test : Pulse width $\leq 300\mu\text{s}$, Duty cycle $\leq 2\%$
4. Essentially independent of operating temperature

Typical Electrical Characteristic

Fig. 1 Typical Output Characteristics

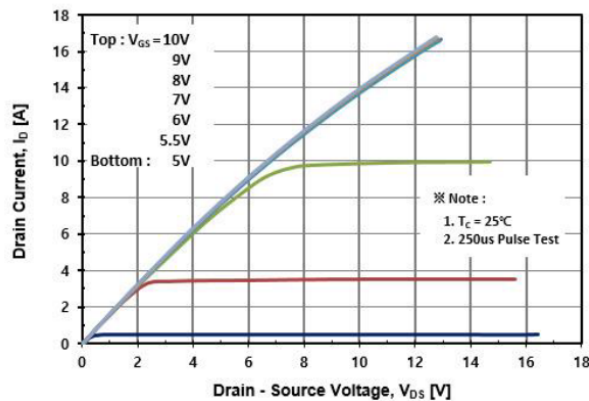


Fig. 2 Typical Output Characteristics

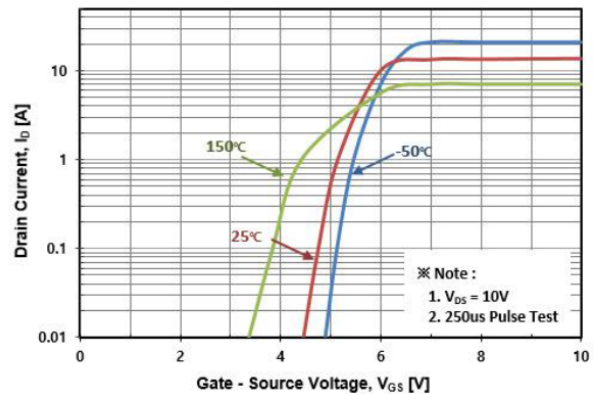


Fig. 3 On-Resistance Variation with Drain Current and Gate Voltage

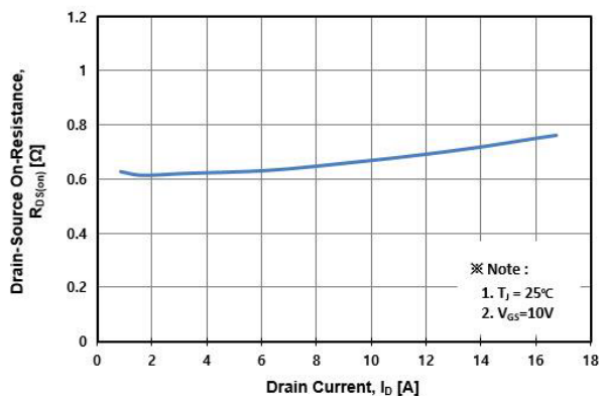


Fig. 4 Body Diode Forward Voltage Variation with Source Current

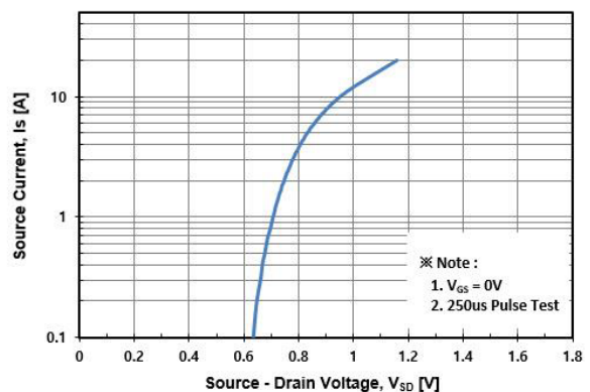


Fig. 5 Typical Capacitance Characteristics

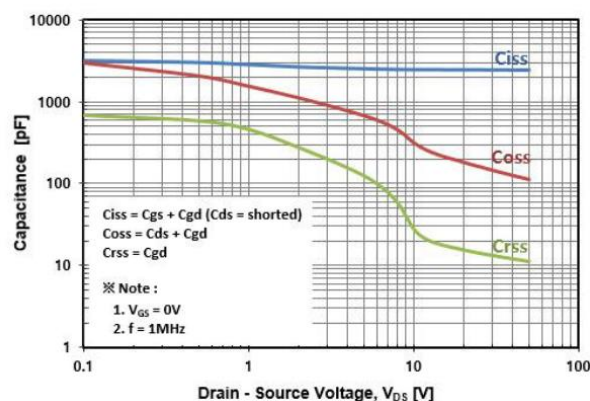
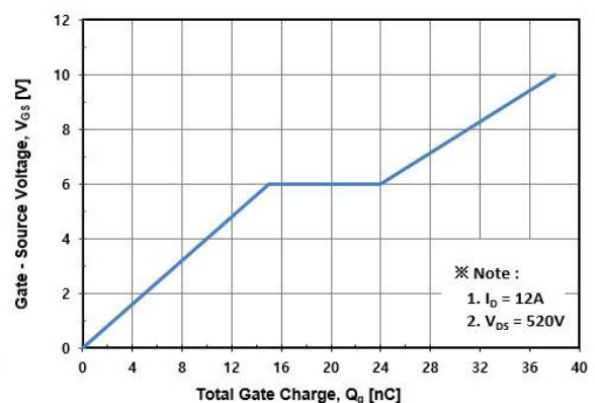


Fig. 6 Typical Total Gate Charge Characteristics





Typical Electrical Characteristic

Fig. 7 Breakdown Voltage Variation vs. Temperature

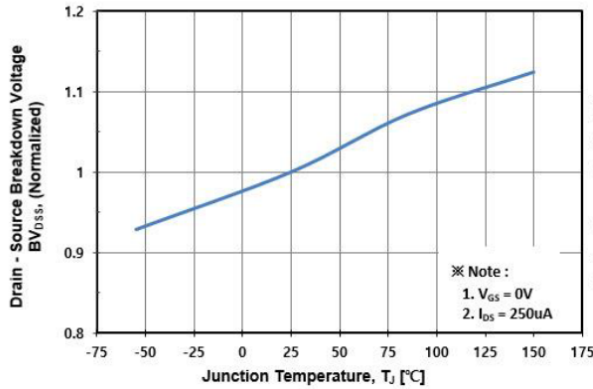


Fig. 8 On-Resistance Variation vs. Temperature

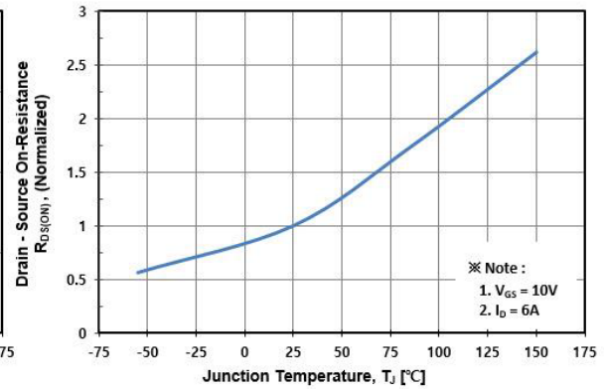


Fig. 9 Maximum Drain Current vs. Case Temperature

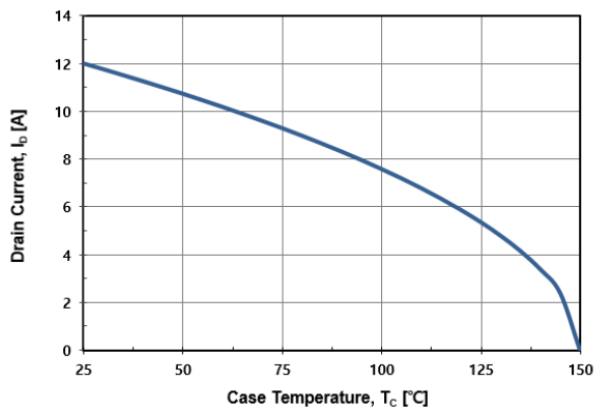


Fig. 10 Maximum Safe Operating Area

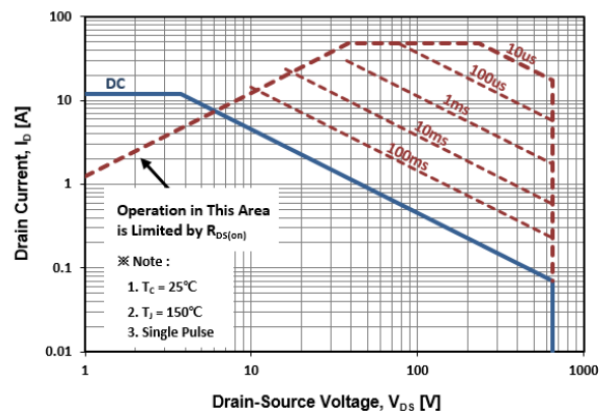


Fig. 11 Transient Thermal Impedance

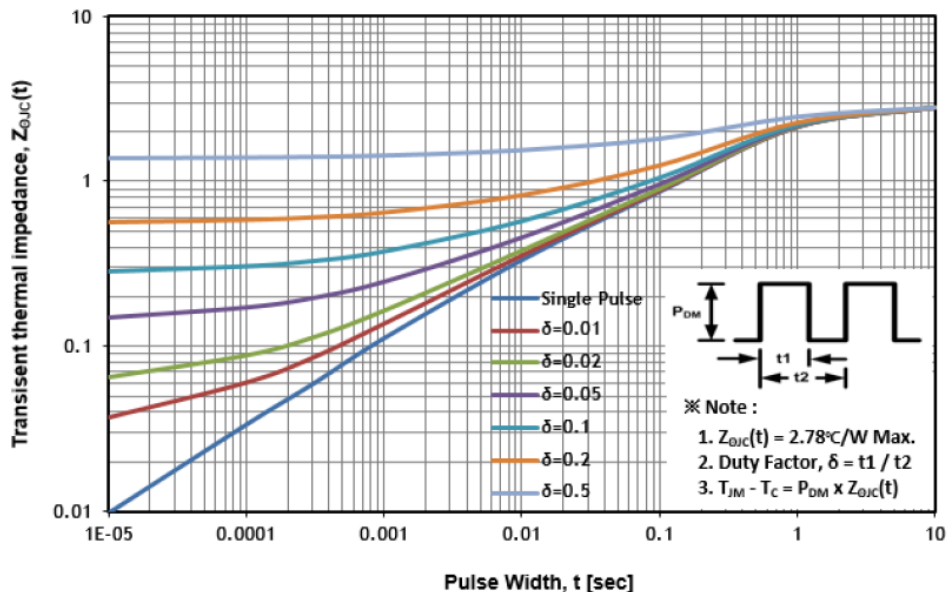




Fig. 12 Gate Charge Test Circuit & Waveform

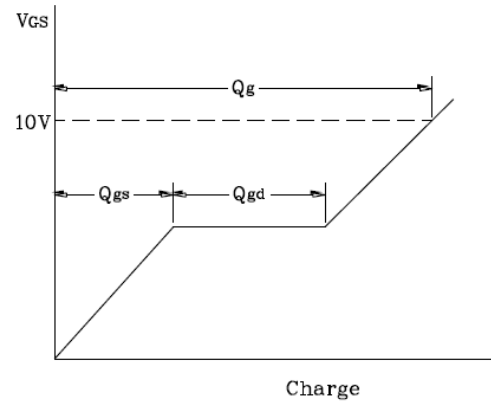
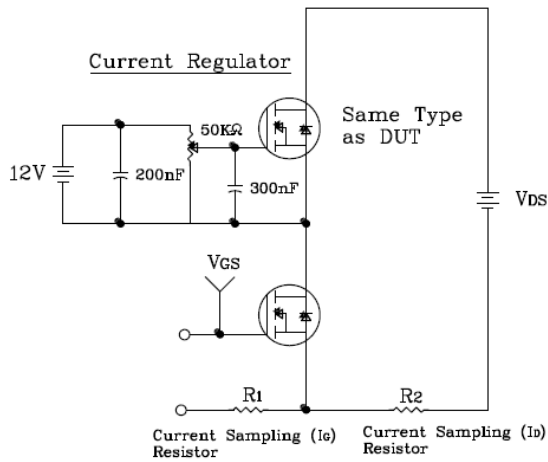


Fig. 13 Resistive Switching Test Circuit & Waveform

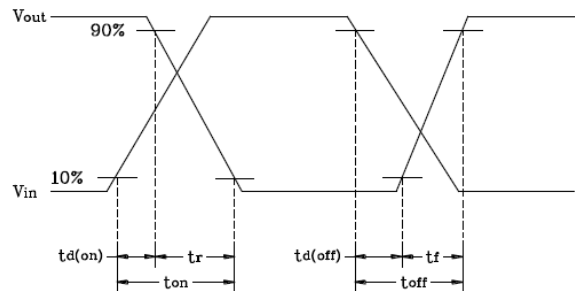
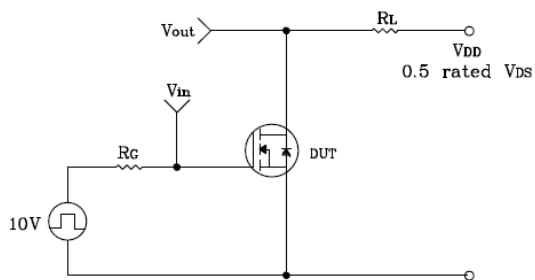


Fig. 14 E_{AS} Test Circuit & Waveform

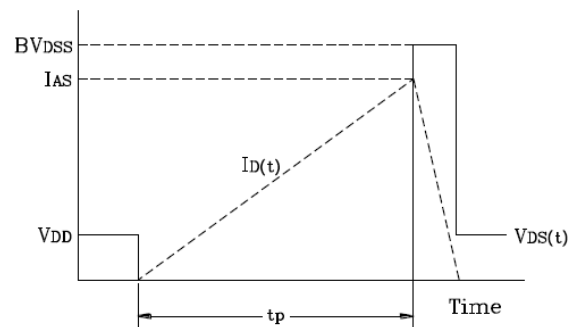
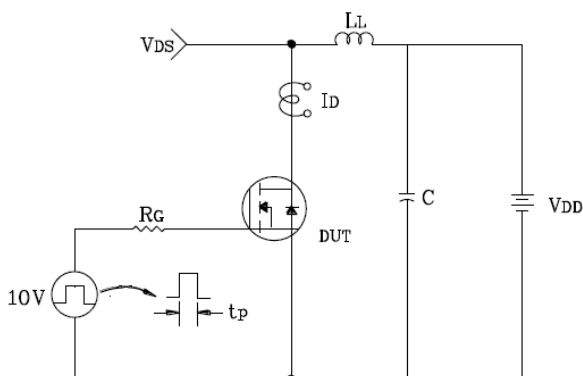
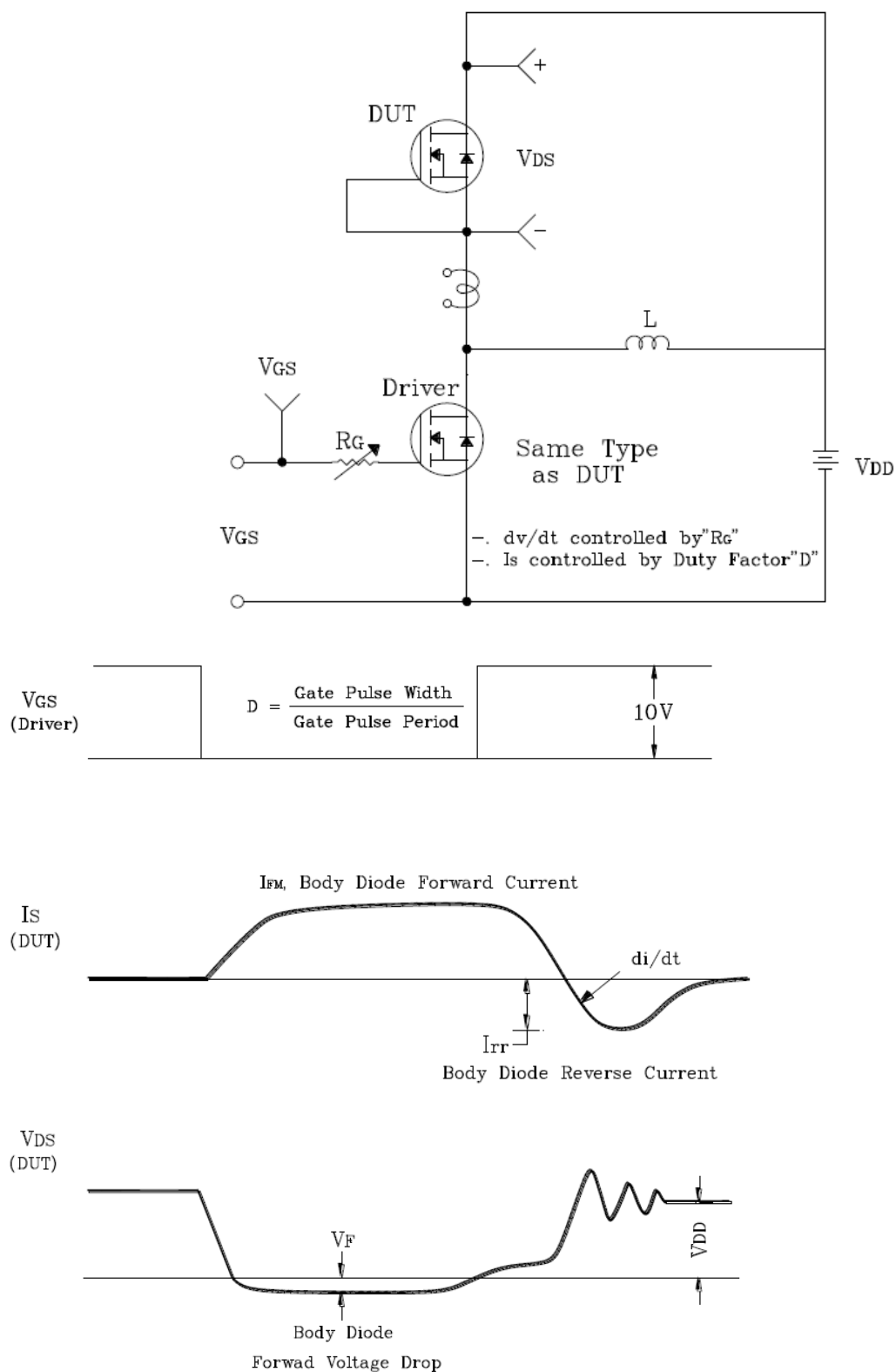


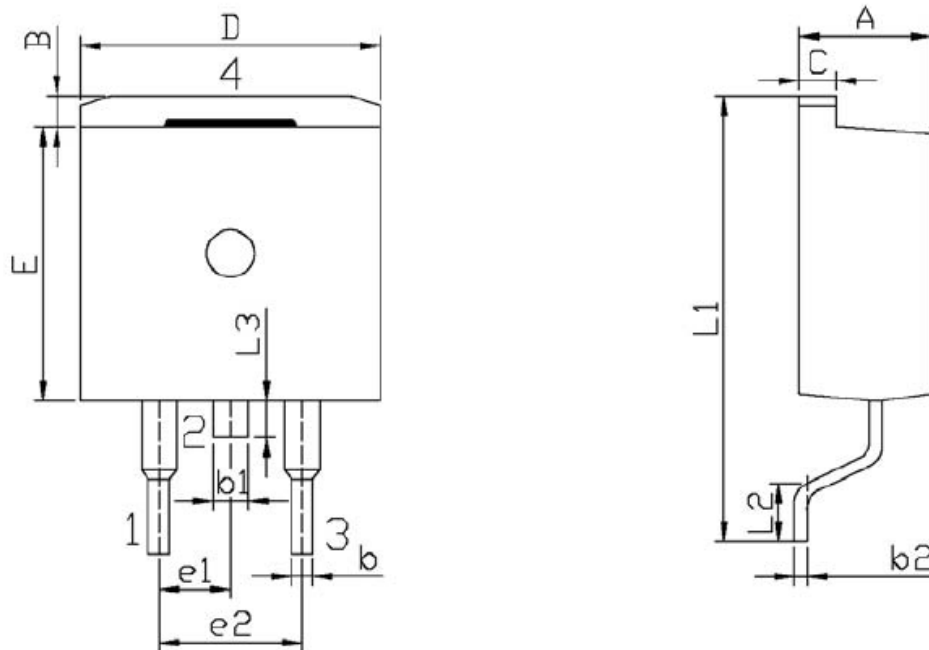
Fig. 15 Diode Reverse Recovery Time Test Circuit & Waveform





Package Dimensions

TO-263 (D₂PAK)



单位: mm

Symbol	Dimensions In Millimeters		Symbol	Dimensions In Millimeters	
	Min	Max		Min	Max
A	4.30	4.70	E	9.00	9.40
B	1.00	1.40	e1	2.34	2.74
b	0.70	0.90	e2	4.88	5.28
b1	1.15	1.35	L1	15.00	16.00
b2	0.40	0.60	L2	2.24	2.84
C	1.20	1.40	L3	1.20	1.60
D	9.80	10.20			



Revision History

No	Date	Contents
0	2023-03-20	Initial Brief Datasheet Release

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